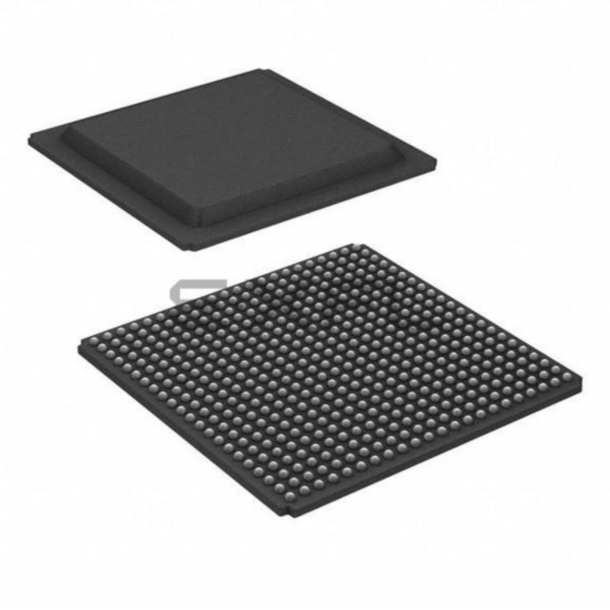
AMD Xilinx - XC6SLX150-L1FG484I Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	11519
Number of Logic Elements/Cells	147443
Total RAM Bits	4939776
Number of I/O	338
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc6slx150-l1fg484i

Table 3: **eFUSE Programming Conditions(1)**

Symbol	Description	Min	Typ	Max	Units
V_{FS}(2)	External voltage supply	3.2	3.3	3.4	V
I_{FS}	V_{FS} supply current	–	–	40	mA
V_{CCAUX}	Auxiliary supply voltage relative to GND	3.2	3.3	3.45	V
R_{FUSE}(3)	External resistor from R_{FUSE} pin to GND	1129	1140	1151	Ω
V_{CCINT}	Internal supply voltage relative to GND	1.14	1.2	1.26	V
t_j	Temperature range	15	–	85	°C

Notes:

1. These specifications apply during programming of the eFUSE AES key. Programming is only supported through JTAG.The AES key is only supported in the following devices: LX75, LX75T, LX100, LX100T, LX150, and LX150T.
2. When programming eFUSE, V_{FS} must be less than or equal to V_{CCAUX}. When not programming or when eFUSE is not used, Xilinx recommends connecting V_{FS} to GND. However, V_{FS} can be between GND and 3.45 V.
3. An R_{FUSE} resistor is required when programming the eFUSE AES key. When not programming or when eFUSE is not used, Xilinx recommends connecting the R_{FUSE} pin to V_{CCAUX} or GND. However, R_{FUSE} can be unconnected.

Table 4: **DC Characteristics Over Recommended Operating Conditions**

<table>
<tr><th>Symbol</th><th colspan="2">Description</th><th>Min</th><th>Typ</th><th>Max</th><th>Units</th></tr>
<tr><td>V_{DRINT}</td><td colspan="2">Data retention V_{CCINT} voltage (below which configuration data might be lost)</td><td>0.8</td><td>–</td><td>–</td><td>V</td></tr>
<tr><td>V_{DRAUX}</td><td colspan="2">Data retention V_{CCAUX} voltage (below which configuration data might be lost)</td><td>2.0</td><td>–</td><td>–</td><td>V</td></tr>
<tr><td rowspan="2">I_{REF}</td><td colspan="2">V_{REF} leakage current per pin for commercial (C) and industrial (I) devices</td><td>–10</td><td>–</td><td>10</td><td>μA</td></tr>
<tr><td colspan="2">V_{REF} leakage current per pin for expanded (Q) devices</td><td>–15</td><td>–</td><td>15</td><td>μA</td></tr>
<tr><td rowspan="2">I_L</td><td colspan="2">Input or output leakage current per pin (sample-tested) for commercial (C) and industrial (I) devices</td><td>–10</td><td>–</td><td>10</td><td>μA</td></tr>
<tr><td colspan="2">Input or output leakage current per pin (sample-tested) for expanded (Q) devices</td><td>–15</td><td>–</td><td>15</td><td>μA</td></tr>
<tr><td rowspan="2">I_{HS}</td><td rowspan="2">Leakage current on pins during hot socketing with FPGA unpowered</td><td>All pins except PROGRAM_B, DONE, and JTAG pins when HSWAPEN = 1</td><td>–20</td><td>–</td><td>20</td><td>μA</td></tr>
<tr><td>PROGRAM_B, DONE, and JTAG pins, or other pins when HSWAPEN = 0</td><td colspan="3">$I_{HS} + I_{RPU}$</td><td>μA</td></tr>
<tr><td>C_{IN}(1)</td><td colspan="2">Die input capacitance at the pad</td><td>–</td><td>–</td><td>10</td><td>pF</td></tr>
<tr><td rowspan="5">I_{RPU}</td><td colspan="2">Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V or V_{CCAUX} = 3.3V</td><td>200</td><td>–</td><td>500</td><td>μA</td></tr>
<tr><td colspan="2">Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V or V_{CCAUX} = 2.5V</td><td>120</td><td>–</td><td>350</td><td>μA</td></tr>
<tr><td colspan="2">Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V</td><td>60</td><td>–</td><td>200</td><td>μA</td></tr>
<tr><td colspan="2">Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V</td><td>40</td><td>–</td><td>150</td><td>μA</td></tr>
<tr><td colspan="2">Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V</td><td>12</td><td>–</td><td>100</td><td>μA</td></tr>
<tr><td rowspan="2">I_{RPD}</td><td colspan="2">Pad pull-down (when selected) @ V_{IN} = V_{CCO}, V_{CCAUX} = 3.3V</td><td>200</td><td>–</td><td>550</td><td>μA</td></tr>
<tr><td colspan="2">Pad pull-down (when selected) @ V_{IN} = V_{CCO}, V_{CCAUX} = 2.5V</td><td>140</td><td>–</td><td>400</td><td>μA</td></tr>
<tr><td>I_{BATT}(2)</td><td colspan="2">Battery supply current</td><td>–</td><td>–</td><td>150</td><td>nA</td></tr>
<tr><td>R_{DT}(3)</td><td colspan="2">Resistance of optional input differential termination circuit, V_{CCAUX} = 3.3V</td><td>–</td><td>100</td><td>–</td><td>Ω</td></tr>
<tr><td rowspan="6">R_{IN_TERM}(5)</td><td colspan="2">Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_25) for commercial (C) and industrial (I) devices</td><td>23</td><td>25</td><td>55</td><td>Ω</td></tr>
<tr><td colspan="2">Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_25) for expanded (Q) devices</td><td>20</td><td>25</td><td>55</td><td>Ω</td></tr>
<tr><td colspan="2">Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_50) for commercial (C) and industrial (I) devices</td><td>39</td><td>50</td><td>72</td><td>Ω</td></tr>
<tr><td colspan="2">Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_50) for expanded (Q) devices</td><td>32</td><td>50</td><td>74</td><td>Ω</td></tr>
<tr><td colspan="2">Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_75) for commercial (C) and industrial (I) devices</td><td>56</td><td>75</td><td>109</td><td>Ω</td></tr>
<tr><td colspan="2">Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_75) for expanded (Q) devices</td><td>47</td><td>75</td><td>115</td><td>Ω</td></tr>
<tr><td rowspan="3">R_{OUT_TERM}</td><td colspan="2">Thevenin equivalent resistance of programmable output termination (UNTUNED_25)</td><td>11</td><td>25</td><td>52</td><td>Ω</td></tr>
<tr><td colspan="2">Thevenin equivalent resistance of programmable output termination (UNTUNED_50)</td><td>21</td><td>50</td><td>96</td><td>Ω</td></tr>
<tr><td colspan="2">Thevenin equivalent resistance of programmable output termination (UNTUNED_75)</td><td>29</td><td>75</td><td>145</td><td>Ω</td></tr>
</table>

Notes:

1. The C_{IN} measurement represents the die capacitance at the pad, not including the package.
2. Maximum value specified for worst case process at 25°C. LX75, LX75T, LX100, LX100T, LX150, and LX150T only.
3. Refer to IBIS models for R_{DT} variation and for values at V_{CCAUX} = 2.5V. IBIS values for R_{DT} are valid for all temperature ranges.
4. V_{CCO2} is not required for data retention. The minimum V_{CCO2} for power-on reset and configuration is 1.65V.
5. Termination resistance to a V_{CCO}/2 level.

SelectIO™ Interface DC Input and Output Levels

Table 7: **Recommended Operating Conditions for User I/Os Using Single-Ended Standards**

I/O Standard	V_{CCO} for Drivers(1)			V_{REF} for Inputs		
	V, Min	V, Nom	V, Max	V, Min	V, Nom	V, Max
LVTTL	3.0	3.3	3.45	V_{REF} is not used for these I/O standards		
LVCMOS33	3.0	3.3	3.45			
LVCMOS25	2.3	2.5	2.7			
LVCMOS18	1.65	1.8	1.95			
LVCMOS18_JEDEC	1.65	1.8	1.95			
LVCMOS15	1.4	1.5	1.6			
LVCMOS15_JEDEC	1.4	1.5	1.6			
LVCMOS12	1.1	1.2	1.3			
LVCMOS12_JEDEC	1.1	1.2	1.3			
PCI33_3(2)	3.0	3.3	3.45			
PCI66_3(2)	3.0	3.3	3.45			
I2C	2.7	3.0	3.45			
SMBUS	2.7	3.0	3.45			
SDIO	3.0	3.3	3.45			
MOBILE_DDR	1.7	1.8	1.9			
HSTL_I	1.4	1.5	1.6	0.68	0.75	0.9
HSTL_II	1.4	1.5	1.6	0.68	0.75	0.9
HSTL_III	1.4	1.5	1.6	–	0.9	–
HSTL_I_18	1.7	1.8	1.9	0.8	0.9	1.1
HSTL_II_18	1.7	1.8	1.9	–	0.9	–
HSTL_III_18	1.7	1.8	1.9	–	1.1	–
SSTL3_I	3.0	3.3	3.45	1.3	1.5	1.7
SSTL3_II	3.0	3.3	3.45	1.3	1.5	1.7
SSTL2_I	2.3	2.5	2.7	1.13	1.25	1.38
SSTL2_II	2.3	2.5	2.7	1.13	1.25	1.38
SSTL18_I	1.7	1.8	1.9	0.833	0.9	0.969
SSTL18_II	1.7	1.8	1.9	0.833	0.9	0.969
SSTL15_II	1.425	1.5	1.575	0.69	0.75	0.81

Notes:

1. V_{CCO} range required when using I/O standard for an output. Also required for MOBILE_DDR, PCI33_3, LVCMOS18_JEDEC, LVCMOS15_JEDEC, and LVCMOS12_JEDEC inputs, and for LVCMOS25 inputs when V_{CCAUX} = 3.3V.
2. For PCI systems, the transmitter and receiver should have common supplies for V_{CCO}.

Table 14: GTP Transceiver Current Supply (per Lane)

Symbol	Description	Typ[(1)]	Max	Units
$I_{MGTAVCC}$	GTP transceiver internal analog supply current	40.4	Note 2	mA
$I_{MGTAVTTTX}$	GTP transmitter termination supply current	27.4		mA
$I_{MGTAVTTRX}$	GTP receiver termination supply current	13.6		mA
$I_{MGTAVCCPLL}$	GTP transmitter and receiver PLL supply current	28.7		mA
$R_{MGTRREF}$	Precision reference resistor for internal calibration termination	50.0 ± 1% tolerance		Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C, with a 2.5 Gb/s line rate, with a shared PLL use mode.
2. Values for currents of other transceiver configurations and conditions can be obtained by using the XPOWER Estimator (XPE) or XPOWER Analyzer (XPA) tools.

Table 15: GTP Transceiver Quiescent Supply Current (per Lane)(1)(2)(3)(4)

Symbol	Description	Typ[(5)]	Max	Units
$I_{MGTAVCCQ}$	Quiescent MGTAVCC supply current	1.7	Note 2	mA
$I_{MGTAVTTTXQ}$	Quiescent MGTAVTTTX supply current	0.1		mA
$I_{MGTAVTTRXQ}$	Quiescent MGTAVTTRX supply current	1.2		mA
$I_{MGTAVCCPLLQ}$	Quiescent MGTAVCCPLL supply current	1.0		mA

Notes:

1. Device powered and unconfigured.
2. Currents for conditions other than values specified in this table can be obtained by using the XPOWER Estimator (XPE) or XPOWER Analyzer (XPA) tools.
3. GTP transceiver quiescent supply current for an entire device can be calculated by multiplying the values in this table by the number of available GTP transceivers.
4. Does not include power-up MGTAVTTRCAL supply current during device configuration.
5. Typical values are specified at nominal voltage, 25°C.

Switching Characteristics

All values represented in this data sheet are based on these speed specifications: v1.20 for -3, -3N, and -2; and v1.08 for -1L. Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Production

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to Production before faster speed grades.

All specifications are always representative of worst-case supply voltage and junction temperature conditions.

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device.

The -1L speed grade refers to the lower-power Spartan-6 devices. The -3N speed grade refers to the Spartan-6 devices that do not support MCB functionality.

Table 26 correlates the current status of each Spartan-6 device on a per speed grade basis.

Table 26: **Spartan-6 Device Speed Grade Designations**

Device	Speed Grade Designations		
	Advance	Preliminary	Production
XC6SLX4[1]			-3, -2, -1L
XC6SLX9			-3, -3N, -2, -1L
XC6SLX16			-3, -3N, -2, -1L
XC6SLX25			-3, -3N, -2, -1L
XC6SLX25T			-3, -3N, -2
XC6SLX45			-3, -3N, -2, -1L
XC6SLX45T			-3, -3N, -2
XC6SLX75			-3, -3N, -2, -1L
XC6SLX75T			-3, -3N, -2
XC6SLX100			-3, -3N, -2, -1L
XC6SLX100T			-3, -3N, -2
XC6SLX150			-3, -3N, -2, -1L
XC6SLX150T			-3, -3N, -2
XA6SLX4			-3, -2
XA6SLX9			-3, -2
XA6SLX16			-3, -2
XA6SLX25			-3, -2
XA6SLX25T			-3, -2
XA6SLX45			-3, -2
XA6SLX45T			-3, -2
XA6SLX75			-3, -2
XA6SLX75T			-3, -2
XA6SLX100			-2
XQ6SLX75			-2, -1L
XQ6SLX75T			-3, -2
XQ6SLX150			-2, -1L
XQ6SLX150T			-3, -2

Notes:

1. The XC6SLX4 is not available in the -3N speed grade.

Testing of Switching Characteristics

All devices are 100% functionally tested. Internal timing parameters are derived from measuring internal test patterns. Listed below are representative values.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Spartan-6 devices.

Table 27: **Spartan-6 Device Production Software and Speed Specification Release[(1)] *(Cont'd)***

Device	Speed Grade Designations[(2)]			
	-3[(3)]	-3N	-2[(4)]	-1L
XQ6SLX75	N/A	N/A	ISE 13.2 v1.19	ISE 13.2 v1.07
XQ6SLX75T	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XQ6SLX150	N/A	N/A	ISE 13.2 v1.19	ISE 13.2 v1.07
XQ6SLX150T	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A

Notes:

1. ISE 13.3 software with v1.20 for -3, -3N, and -2; and v1.08 for -1L speed specification reflects the changes outlined in XCN11028: *Spartan-6 FPGA Speed File Changes*.
2. As marked with an N/A, LXT devices and all XA devices are not available with a -1L speed grade; LX4 devices and all XA and XQ devices are not available with a -3N speed grade.
3. Improved -3 specifications reflected in this data sheet require ISE 12.4 software with v1.15 speed specification.
4. Improved -2 specifications reflected in this data sheet require ISE 12.4 software and the *12.4 Speed Files Patch* which contains the v1.17 speed specification available on the Xilinx Download Center.
5. ISE 12.3 software with v1.12 speed specification is available using ISE 12.3 software and the *12.3 Speed Files Patch* available on the Xilinx Download Center.
6. ISE 12.2 software with v1.11 speed specification is available using ISE 12.2 software and the *12.2 Speed Files Patch* available on the Xilinx Download Center.
7. ISE 13.1 software with v1.18 speed specification is available using ISE 13.1 software and the *13.1 Update* available on the Xilinx Download Center. See XCN11012: *Speed File Change for -3N Devices*.

IOB Pad Input/Output/3-State Switching Characteristics

Table 28 (for commercial (XC) Spartan-6 devices) and Table 29 (for Automotive XA Spartan-6 and Defense-grade Spartan-6Q devices) summarizes the values of standard-specific data input delays, output delays terminating at pads (based on standard), and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer.

See the TRACE report for further information on delays when using an I/O standard with UNTUNED termination on inputs or outputs.

Table 28: **IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices**

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L[(1)]	-3	-3N	-2	-1L[(1)]	-3	-3N	-2	-1L[(1)]	
LVDS_33	1.17	1.29	1.42	1.68	1.55	1.69	1.89	2.42	3000	3000	3000	3000	ns
LVDS_25	1.01	1.13	1.26	1.57	1.65	1.79	1.99	2.47	3000	3000	3000	3000	ns
BLVDS_25	1.02	1.14	1.27	1.57	1.72	1.86	2.06	2.68	1.72	1.86	2.06	2.68	ns
MINI_LVDS_33	1.17	1.29	1.42	1.68	1.57	1.71	1.91	2.41	3000	3000	3000	3000	ns
MINI_LVDS_25	1.01	1.13	1.26	1.57	1.65	1.79	1.99	2.47	3000	3000	3000	3000	ns
LVPECL_33	1.18	1.30	1.43	1.68	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVPECL_25	1.02	1.14	1.27	1.57	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
RSDS_33 (point to point)	1.17	1.29	1.42	1.68	1.57	1.71	1.91	2.42	3000	3000	3000	3000	ns
RSDS_25 (point to point)	1.01	1.13	1.26	1.56	1.65	1.79	1.99	2.47	3000	3000	3000	3000	ns
TMDS_33	1.21	1.33	1.46	1.71	1.54	1.68	1.88	2.50	3000	3000	3000	3000	ns

Table 28: **IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L(1)	-3	-3N	-2	-1L(1)	-3	-3N	-2	-1L(1)	
LVCMOS33, Fast, 8 mA	1.34	1.46	1.59	1.82	2.07	2.21	2.41	3.03	2.07	2.21	2.41	3.03	ns
LVCMOS33, Fast, 12 mA	1.34	1.46	1.59	1.82	1.65	1.79	1.99	2.62	1.65	1.79	1.99	2.62	ns
LVCMOS33, Fast, 16 mA	1.34	1.46	1.59	1.82	1.65	1.79	1.99	2.62	1.65	1.79	1.99	2.62	ns
LVCMOS33, Fast, 24 mA	1.34	1.46	1.59	1.82	1.65	1.79	1.99	2.62	1.65	1.79	1.99	2.62	ns
LVCMOS25, QUIETIO, 2 mA	0.82	0.94	1.07	1.31	4.81	4.95	5.15	5.79	4.81	4.95	5.15	5.79	ns
LVCMOS25, QUIETIO, 4 mA	0.82	0.94	1.07	1.31	3.70	3.84	4.04	4.66	3.70	3.84	4.04	4.66	ns
LVCMOS25, QUIETIO, 6 mA	0.82	0.94	1.07	1.31	3.46	3.60	3.80	4.38	3.46	3.60	3.80	4.38	ns
LVCMOS25, QUIETIO, 8 mA	0.82	0.94	1.07	1.31	3.20	3.34	3.54	4.12	3.20	3.34	3.54	4.12	ns
LVCMOS25, QUIETIO, 12 mA	0.82	0.94	1.07	1.31	2.83	2.97	3.17	3.75	2.83	2.97	3.17	3.75	ns
LVCMOS25, QUIETIO, 16 mA	0.82	0.94	1.07	1.31	2.64	2.78	2.98	3.64	2.64	2.78	2.98	3.64	ns
LVCMOS25, QUIETIO, 24 mA	0.82	0.94	1.07	1.31	2.45	2.59	2.79	3.42	2.45	2.59	2.79	3.42	ns
LVCMOS25, Slow, 2 mA	0.82	0.94	1.07	1.31	3.78	3.92	4.12	4.76	3.78	3.92	4.12	4.76	ns
LVCMOS25, Slow, 4 mA	0.82	0.94	1.07	1.31	2.79	2.93	3.13	3.73	2.79	2.93	3.13	3.73	ns
LVCMOS25, Slow, 6 mA	0.82	0.94	1.07	1.31	2.73	2.87	3.07	3.66	2.73	2.87	3.07	3.66	ns
LVCMOS25, Slow, 8 mA	0.82	0.94	1.07	1.31	2.48	2.62	2.82	3.42	2.48	2.62	2.82	3.42	ns
LVCMOS25, Slow, 12 mA	0.82	0.94	1.07	1.31	2.01	2.15	2.35	2.95	2.01	2.15	2.35	2.95	ns
LVCMOS25, Slow, 16 mA	0.82	0.94	1.07	1.31	2.01	2.15	2.35	2.95	2.01	2.15	2.35	2.95	ns
LVCMOS25, Slow, 24 mA	0.82	0.94	1.07	1.31	2.01	2.15	2.35	2.94	2.01	2.15	2.35	2.94	ns
LVCMOS25, Fast, 2 mA	0.82	0.94	1.07	1.31	3.35	3.49	3.69	4.31	3.35	3.49	3.69	4.31	ns
LVCMOS25, Fast, 4 mA	0.82	0.94	1.07	1.31	2.25	2.39	2.59	3.22	2.25	2.39	2.59	3.22	ns
LVCMOS25, Fast, 6 mA	0.82	0.94	1.07	1.31	2.09	2.23	2.43	3.05	2.09	2.23	2.43	3.05	ns
LVCMOS25, Fast, 8 mA	0.82	0.94	1.07	1.31	2.02	2.16	2.36	2.98	2.02	2.16	2.36	2.98	ns
LVCMOS25, Fast, 12 mA	0.82	0.94	1.07	1.31	1.56	1.70	1.90	2.52	1.56	1.70	1.90	2.52	ns
LVCMOS25, Fast, 16 mA	0.82	0.94	1.07	1.31	1.56	1.70	1.90	2.52	1.56	1.70	1.90	2.52	ns
LVCMOS25, Fast, 24 mA	0.82	0.94	1.07	1.31	1.56	1.70	1.90	2.52	1.56	1.70	1.90	2.52	ns
LVCMOS18, QUIETIO, 2 mA	1.18	1.30	1.43	2.04	5.92	6.06	6.26	6.80	5.92	6.06	6.26	6.80	ns
LVCMOS18, QUIETIO, 4 mA	1.18	1.30	1.43	2.04	4.74	4.88	5.08	5.63	4.74	4.88	5.08	5.63	ns
LVCMOS18, QUIETIO, 6 mA	1.18	1.30	1.43	2.04	4.05	4.19	4.39	4.96	4.05	4.19	4.39	4.96	ns
LVCMOS18, QUIETIO, 8 mA	1.18	1.30	1.43	2.04	3.71	3.85	4.05	4.63	3.71	3.85	4.05	4.63	ns
LVCMOS18, QUIETIO, 12 mA	1.18	1.30	1.43	2.04	3.35	3.49	3.69	4.27	3.35	3.49	3.69	4.27	ns
LVCMOS18, QUIETIO, 16 mA	1.18	1.30	1.43	2.04	3.20	3.34	3.54	4.14	3.20	3.34	3.54	4.14	ns
LVCMOS18, QUIETIO, 24 mA	1.18	1.30	1.43	2.04	2.96	3.10	3.30	3.98	2.96	3.10	3.30	3.98	ns
LVCMOS18, Slow, 2 mA	1.18	1.30	1.43	2.04	4.62	4.76	4.96	5.54	4.62	4.76	4.96	5.54	ns
LVCMOS18, Slow, 4 mA	1.18	1.30	1.43	2.04	3.69	3.83	4.03	4.60	3.69	3.83	4.03	4.60	ns
LVCMOS18, Slow, 6 mA	1.18	1.30	1.43	2.04	3.00	3.14	3.34	3.94	3.00	3.14	3.34	3.94	ns
LVCMOS18, Slow, 8 mA	1.18	1.30	1.43	2.04	2.19	2.33	2.53	3.17	2.19	2.33	2.53	3.17	ns
LVCMOS18, Slow, 12 mA	1.18	1.30	1.43	2.04	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18, Slow, 16 mA	1.18	1.30	1.43	2.04	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns

Table 28: **IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L(1)	-3	-3N	-2	-1L(1)	-3	-3N	-2	-1L(1)	
LVCMOS18, Slow, 24 mA	1.18	1.30	1.43	2.04	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18, Fast, 2 mA	1.18	1.30	1.43	2.04	3.59	3.73	3.93	4.53	3.59	3.73	3.93	4.53	ns
LVCMOS18, Fast, 4 mA	1.18	1.30	1.43	2.04	2.39	2.53	2.73	3.35	2.39	2.53	2.73	3.35	ns
LVCMOS18, Fast, 6 mA	1.18	1.30	1.43	2.04	1.88	2.02	2.22	2.84	1.88	2.02	2.22	2.84	ns
LVCMOS18, Fast, 8 mA	1.18	1.30	1.43	2.04	1.81	1.95	2.15	2.77	1.81	1.95	2.15	2.77	ns
LVCMOS18, Fast, 12 mA	1.18	1.30	1.43	2.04	1.71	1.85	2.05	2.67	1.71	1.85	2.05	2.67	ns
LVCMOS18, Fast, 16 mA	1.18	1.30	1.43	2.04	1.71	1.85	2.05	2.67	1.71	1.85	2.05	2.67	ns
LVCMOS18, Fast, 24 mA	1.18	1.30	1.43	2.04	1.71	1.85	2.05	2.67	1.71	1.85	2.05	2.67	ns
LVCMOS18_JEDEC, QUIETIO, 2 mA	0.94	1.06	1.19	1.41	5.91	6.05	6.25	6.79	5.91	6.05	6.25	6.79	ns
LVCMOS18_JEDEC, QUIETIO, 4 mA	0.94	1.06	1.19	1.41	4.75	4.89	5.09	5.64	4.75	4.89	5.09	5.64	ns
LVCMOS18_JEDEC, QUIETIO, 6 mA	0.94	1.06	1.19	1.41	4.04	4.18	4.38	4.96	4.04	4.18	4.38	4.96	ns
LVCMOS18_JEDEC, QUIETIO, 8 mA	0.94	1.06	1.19	1.41	3.71	3.85	4.05	4.62	3.71	3.85	4.05	4.62	ns
LVCMOS18_JEDEC, QUIETIO, 12 mA	0.94	1.06	1.19	1.41	3.35	3.49	3.69	4.28	3.35	3.49	3.69	4.28	ns
LVCMOS18_JEDEC, QUIETIO, 16 mA	0.94	1.06	1.19	1.41	3.20	3.34	3.54	4.13	3.20	3.34	3.54	4.13	ns
LVCMOS18_JEDEC, QUIETIO, 24 mA	0.94	1.06	1.19	1.41	2.96	3.10	3.30	3.98	2.96	3.10	3.30	3.98	ns
LVCMOS18_JEDEC, Slow, 2 mA	0.94	1.06	1.19	1.41	4.59	4.73	4.93	5.54	4.59	4.73	4.93	5.54	ns
LVCMOS18_JEDEC, Slow, 4 mA	0.94	1.06	1.19	1.41	3.69	3.83	4.03	4.60	3.69	3.83	4.03	4.60	ns
LVCMOS18_JEDEC, Slow, 6 mA	0.94	1.06	1.19	1.41	3.00	3.14	3.34	3.94	3.00	3.14	3.34	3.94	ns
LVCMOS18_JEDEC, Slow, 8 mA	0.94	1.06	1.19	1.41	2.19	2.33	2.53	3.18	2.19	2.33	2.53	3.18	ns
LVCMOS18_JEDEC, Slow, 12 mA	0.94	1.06	1.19	1.41	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18_JEDEC, Slow, 16 mA	0.94	1.06	1.19	1.41	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18_JEDEC, Slow, 24 mA	0.94	1.06	1.19	1.41	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18_JEDEC, Fast, 2 mA	0.94	1.06	1.19	1.41	3.57	3.71	3.91	4.52	3.57	3.71	3.91	4.52	ns
LVCMOS18_JEDEC, Fast, 4 mA	0.94	1.06	1.19	1.41	2.39	2.53	2.73	3.35	2.39	2.53	2.73	3.35	ns
LVCMOS18_JEDEC, Fast, 6 mA	0.94	1.06	1.19	1.41	1.88	2.02	2.22	2.84	1.88	2.02	2.22	2.84	ns
LVCMOS18_JEDEC, Fast, 8 mA	0.94	1.06	1.19	1.41	1.80	1.94	2.14	2.76	1.80	1.94	2.14	2.76	ns
LVCMOS18_JEDEC, Fast, 12 mA	0.94	1.06	1.19	1.41	1.72	1.86	2.06	2.68	1.72	1.86	2.06	2.68	ns
LVCMOS18_JEDEC, Fast, 16 mA	0.94	1.06	1.19	1.41	1.72	1.86	2.06	2.68	1.72	1.86	2.06	2.68	ns
LVCMOS18_JEDEC, Fast, 24 mA	0.94	1.06	1.19	1.41	1.72	1.86	2.06	2.68	1.72	1.86	2.06	2.68	ns
LVCMOS15, QUIETIO, 2 mA	0.98	1.10	1.23	1.79	5.47	5.61	5.81	6.38	5.47	5.61	5.81	6.38	ns
LVCMOS15, QUIETIO, 4 mA	0.98	1.10	1.23	1.79	4.61	4.75	4.95	5.51	4.61	4.75	4.95	5.51	ns
LVCMOS15, QUIETIO, 6 mA	0.98	1.10	1.23	1.79	4.07	4.21	4.41	4.97	4.07	4.21	4.41	4.97	ns
LVCMOS15, QUIETIO, 8 mA	0.98	1.10	1.23	1.79	3.91	4.05	4.25	4.81	3.91	4.05	4.25	4.81	ns
LVCMOS15, QUIETIO, 12 mA	0.98	1.10	1.23	1.79	3.53	3.67	3.87	4.51	3.53	3.67	3.87	4.51	ns
LVCMOS15, QUIETIO, 16 mA	0.98	1.10	1.23	1.79	3.32	3.46	3.66	4.31	3.32	3.46	3.66	4.31	ns
LVCMOS15, Slow, 2 mA	0.98	1.10	1.23	1.79	4.18	4.32	4.52	5.11	4.18	4.32	4.52	5.11	ns
LVCMOS15, Slow, 4 mA	0.98	1.10	1.23	1.79	3.42	3.56	3.76	4.34	3.42	3.56	3.76	4.34	ns
LVCMOS15, Slow, 6 mA	0.98	1.10	1.23	1.79	2.29	2.43	2.63	3.24	2.29	2.43	2.63	3.24	ns

Table 29: **IOB Switching Characteristics for the Automotive XA Spartan-6 and the Spartan-6Q Devices[1] *(Cont'd)***

I/O Standard	T_{IOPI}		T_{IOOP}		T_{IOTP}		Units
	Speed Grade		Speed Grade		Speed Grade		
	-3	-2	-3	-2	-3	-2	
LVCMOS12, QUIETIO, 6 mA	0.98	1.16	4.79	4.99	4.79	4.99	ns
LVCMOS12, QUIETIO, 8 mA	0.98	1.16	4.43	4.63	4.43	4.63	ns
LVCMOS12, QUIETIO, 12 mA	0.98	1.16	4.18	4.38	4.18	4.38	ns
LVCMOS12, Slow, 2 mA	0.98	1.16	5.12	5.32	5.12	5.32	ns
LVCMOS12, Slow, 4 mA	0.98	1.16	3.00	3.20	3.00	3.20	ns
LVCMOS12, Slow, 6 mA	0.98	1.16	2.91	3.11	2.91	3.11	ns
LVCMOS12, Slow, 8 mA	0.98	1.16	2.51	2.71	2.51	2.71	ns
LVCMOS12, Slow, 12 mA	0.98	1.16	2.25	2.45	2.25	2.45	ns
LVCMOS12, Fast, 2 mA	0.98	1.16	3.60	3.80	3.60	3.80	ns
LVCMOS12, Fast, 4 mA	0.98	1.16	2.49	2.69	2.49	2.69	ns
LVCMOS12, Fast, 6 mA	0.98	1.16	1.94	2.14	1.94	2.14	ns
LVCMOS12, Fast, 8 mA	0.98	1.16	1.82	2.02	1.82	2.02	ns
LVCMOS12, Fast, 12 mA	0.98	1.16	1.80	2.00	1.80	2.00	ns
LVCMOS12_JEDEC, QUIETIO, 2 mA	1.57	1.75	6.53	6.73	6.53	6.73	ns
LVCMOS12_JEDEC, QUIETIO, 4 mA	1.57	1.75	5.12	5.32	5.12	5.32	ns
LVCMOS12_JEDEC, QUIETIO, 6 mA	1.57	1.75	4.81	5.01	4.81	5.01	ns
LVCMOS12_JEDEC, QUIETIO, 8 mA	1.57	1.75	4.44	4.64	4.44	4.64	ns
LVCMOS12_JEDEC, QUIETIO, 12 mA	1.57	1.75	4.20	4.40	4.20	4.40	ns
LVCMOS12_JEDEC, Slow, 2 mA	1.57	1.75	5.14	5.34	5.14	5.34	ns
LVCMOS12_JEDEC, Slow, 4 mA	1.57	1.75	2.99	3.19	2.99	3.19	ns
LVCMOS12_JEDEC, Slow, 6 mA	1.57	1.75	2.90	3.10	2.90	3.10	ns
LVCMOS12_JEDEC, Slow, 8 mA	1.57	1.75	2.50	2.70	2.50	2.70	ns
LVCMOS12_JEDEC, Slow, 12 mA	1.57	1.75	2.26	2.46	2.26	2.46	ns
LVCMOS12_JEDEC, Fast, 2 mA	1.57	1.75	3.60	3.80	3.60	3.80	ns
LVCMOS12_JEDEC, Fast, 4 mA	1.57	1.75	2.49	2.69	2.49	2.69	ns
LVCMOS12_JEDEC, Fast, 6 mA	1.57	1.75	1.94	2.14	1.94	2.14	ns
LVCMOS12_JEDEC, Fast, 8 mA	1.57	1.75	1.83	2.03	1.83	2.03	ns
LVCMOS12_JEDEC, Fast, 12 mA	1.57	1.75	1.80	2.00	1.80	2.00	ns

Notes:

1. The Spartan-6Q FPGA -1L values are listed in Table 28.

Table 30 summarizes the value of T_{IOTPHZ}. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). These delays are measured using LVCMOS25, Fast, 12 mA.

Table 30: **IOB 3-state ON Output Switching Characteristics (T_{IOTPHZ})**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
T_{IOTPHZ}	T input to Pad high-impedance	1.39	1.59	1.59	1.91	ns

I/O Standard Measurement Methodology

Input Delay Measurements

Table 31 shows the test setup parameters used for measuring input delay.

Table 31: **Input Delay Measurement Methodology**

Description	I/O Standard Attribute	V_L[1]	V_H[1]	V_{MEAS}[3][4]	V_{REF}[2][4]
LVTTL (Low-Voltage Transistor-Transistor Logic)	LVTTL	0	3.0	1.4	–
LVCMOS (Low-Voltage CMOS), 3.3V	LVCMOS33	0	3.3	1.65	–
LVCMOS, 2.5V	LVCMOS25	0	2.5	1.25	–
LVCMOS, 1.8V	LVCMOS18	0	1.8	0.9	–
LVCMOS, 1.5V	LVCMOS15	0	1.5	0.75	–
LVCMOS, 1.2V	LVCMOS12	0	1.2	0.6	–
PCI (Peripheral Component Interface), 33 MHz and 66 MHz, 3.3V	PCI33_3, PCI66_3	Per PCI Specification			–
HSTL (High-Speed Transceiver Logic), Class I & II	HSTL_I, HSTL_II	$V_{REF} - 0.5$	$V_{REF} + 0.5$	V_{REF}	0.75
HSTL, Class III	HSTL_III	$V_{REF} - 0.5$	$V_{REF} + 0.5$	V_{REF}	0.90
HSTL, Class I & II, 1.8V	HSTL_I_18, HSTL_II_18	$V_{REF} - 0.5$	$V_{REF} + 0.5$	V_{REF}	0.90
HSTL, Class III 1.8V	HSTL_III_18	$V_{REF} - 0.5$	$V_{REF} + 0.5$	V_{REF}	1.1
SSTL (Stub Terminated Transceiver Logic), Class I & II, 3.3V	SSTL3_I, SSTL3_II	$V_{REF} - 0.75$	$V_{REF} + 0.75$	V_{REF}	1.5
SSTL, Class I & II, 2.5V	SSTL2_I, SSTL2_II	$V_{REF} - 0.75$	$V_{REF} + 0.75$	V_{REF}	1.25
SSTL, Class I & II, 1.8V	SSTL18_I, SSTL18_II	$V_{REF} - 0.5$	$V_{REF} + 0.5$	V_{REF}	0.90
SSTL, Class II, 1.5V	SSTL15_II	$V_{REF} - 0.2$	$V_{REF} + 0.2$	V_{REF}	0.75
LVDS (Low-Voltage Differential Signaling), 2.5V & 3.3V	LVDS_25, LVDS_33	1.25 – 0.125	1.25 + 0.125	0[5]	–
LVPECL (Low-Voltage Positive Emitter-Coupled Logic), 2.5V & 3.3V	LVPECL_25, LVPECL_33	1.2 – 0.3	1.2 + 0.3	0[5]	–
BLVDS (Bus LVDS), 2.5V	BLVDS_25	1.3 – 0.125	1.3 + 0.125	0[5]	–
Mini-LVDS, 2.5V & 3.3V	MINI_LVDS_25, MINI_LVDS_33	1.2 – 0.125	1.2 + 0.125	0[5]	–
RSDS (Reduced Swing Differential Signaling), 2.5V & 3.3V	RSDS_25, RSDS_33	1.2 – 0.1	1.2 + 0.1	0[5]	–
TMDS (Transition Minimized Differential Signaling), 3.3V	TMDS_33	3.0 – 0.1	3.0 + 0.1	0[5]	–
PPDS (Point-to-Point Differential Signaling, 2.5V & 3.3V	PPDS_25, PPDS_33	1.25 – 0.1	1.25 + 0.1	0[5]	–

Notes:

1. Input waveform switches between V_L and V_H.
2. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst case of these measurements. V_{REF} values listed are typical.
3. Input voltage level from which measurement starts.
4. This is an input voltage reference that bears no relation to the V_{REF} / V_{MEAS} parameters found in IBIS models and/or noted in Figure 4.
5. The value given is the differential input voltage.

Table 32: **Output Delay Measurement Methodology *(Cont'd)***

Description	I/O Standard Attribute	R_{REF} (Ω)	C_{REF}[1] (pF)	V_{MEAS} (V)	V_{REF} (V)
SSTL, Class II, 2.5V	SSTL2_II	25	0	V_{REF}	1.25
SSTL, Class II, 1.5V	SSTL15_II	25	0	V_{REF}	0.75
LVDS (Low-Voltage Differential Signaling), 2.5V & 3.3V	LVDS_25, LVDS_33	100	0	0(3)	–
BLVDS (Bus LVDS), 2.5V	BLVDS_25	Note 4	0	0(3)	–
Mini-LVDS, 2.5V & 3.3V	MINI_LVDS_25, MINI_LVDS_33	100	0	0(3)	–
RSDS (Reduced Swing Differential Signaling), 2.5V & 3.3V	RSDS_25, RSDS_33	100	0	0(3)	–
TMDS (Transition Minimized Differential Signaling), 3.3V	TMDS_33	Note 5	0	0(3)	–
PPDS (Point-to-Point Differential Signaling, 2.5V & 3.3V	PPDS_25, PPDS_33	100	0	0(3)	–

Notes:

1. C_{REF} is the capacitance of the probe, nominally 0 pF.
2. Per PCI specifications.
3. The value given is the differential output voltage.
4. See the *BLVDS Output Termination* section in UG381, *Spartan-6 FPGA SelectIO Resources User Guide.*
5. See the *TMDS_33 Termination* section in UG381, *Spartan-6 FPGA SelectIO Resources User Guide.*

Simultaneously Switching Outputs

Due to package electrical parasitics, a given package supports a limited number of simultaneous switching outputs (SSOs) when using fast, high-drive outputs. Table 33 and Table 34 provide guidelines for the recommended maximum allowable number of SSOs. These guidelines describe the maximum number of user I/O pins of an output signal standard that should simultaneously switch in the same direction, while maintaining a safe level of switching noise for that particular signal standard. Meeting these guidelines for the stated test conditions ensures that the FPGA operates free from the adverse effects of GND and power bounce.

For each device/package combination, Table 33 provides the number of equivalent V_{CCO}/GND pairs per bank. For each output signal standard and drive strength, Table 34 recommends the maximum number of SSOs, switching in the same direction, allowed per V_{CCO}/GND pair within an I/O bank. The guidelines are categorized by package style, slew rate, and output drive current. The number of SSOs are also specified by I/O bank. Multiply the appropriate numbers from each table to calculate the maximum number of SSOs allowed within an I/O bank. The guidelines assume that all pins within a bank use the same I/O standard. Exceeding these SSO guidelines can result in increased power or GND bounce, degraded signal integrity, or increased system jitter. For a given I/O standard, if the SSO limit per pair in Table 34 is greater than the maximum I/O per pair in Table 33, then there is no SSO limit for the exclusive use of that I/O standard.

The recommended maximum SSO values assume that the FPGA is soldered on a printed circuit board and that the board uses sound design practices. Due to the additional inductance introduced by the socket, the SSO values do not apply for FPGAs mounted in sockets. The SSO values assume that the V_{CCAUX} is powered at 3.3V. Setting V_{CCAUX} to 2.5V provides better SSO characteristics. For more detail, see UG381: *Spartan-6 FPGA SelectIO Resources User Guide.*

Table 34: **SSO Limit per V_{CCO}/GND Pair *(Cont'd)***

V_{CCO}	I/O Standard	Drive	Slew	SSO Limit per V_{CCO}/GND Pair			
				All TQG144, CPG196, CSG225, FT(G)256, and LX devices in CSG324		All CS(G)484, FG(G)484, FG(G)676, FG(G)900, and LXT devices in CSG324	
				Bank 0/2	Bank 1/3	Bank 0/2	Bank 1/3/4/5
3.3V	LVTTL	2	Fast	53	65	53	62
			Slow	70	80	70	73
			QuietIO	79	89	79	91
		4	Fast	23	30	23	27
			Slow	34	41	34	37
			QuietIO	44	49	44	46
		6	Fast	16	21	16	20
			Slow	21	28	21	25
			QuietIO	34	39	34	34
		8	Fast	12	16	12	15
			Slow	16	22	16	19
			QuietIO	27	28	27	24
		12	Fast	1	3	1	1
			Slow	2	5	2	4
			QuietIO	2	10	2	8
		16	Fast	1	3	1	1
			Slow	1	7	1	2
			QuietIO	3	11	3	8
		24	Fast	1	2	1	1
			Slow	2	5	2	2
			QuietIO	8	9	8	8
	PCI33_3			18	19	18	19
	PCI66_3			18	19	18	19
	SSTL_3_I			5	8	5	8
	SSTL_3_II			3	5	3	3
	DIFF_SSTL_3_I			15	24	15	24
	DIFF_SSTL_3_II			9	15	9	9
	SDIO			17	18	17	15

Input/Output Delay Switching Characteristics

Table 39: **IODELAY2 Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L[3]	
T_{IODCCK_CAL} / T_{IODCKC_CAL}	CAL pin Setup/Hold with respect to CK	0.28/ –0.13	0.33/ –0.13	0.48/ –0.13	N/A	ns
T_{IODCCK_CE} / T_{IODCKC_CE}	CE pin Setup/Hold with respect to CK	0.17/ –0.03	0.17/ –0.03	0.25/ –0.02	N/A	ns
T_{IODCCK_INC}/ T_{IODCKC_INC}	INC pin Setup/Hold with respect to CK	0.10/ 0.02	0.12/ 0.03	0.18/ 0.06	N/A	ns
T_{IODCCK_RST}/ T_{IODCKC_RST}	RST pin Setup/Hold with respect to CK	0.12/ –0.02	0.15/ –0.02	0.22/ –0.01	N/A	ns
T_{TAP1}[2]	Maximum tap 1 delay	8	14	16	N/A	ps
T_{TAP2}	Maximum tap 2 delay	40	66	77	N/A	ps
T_{TAP3}	Maximum tap 3 delay	95	120	140	N/A	ps
T_{TAP4}	Maximum tap 4 delay	108	141	166	N/A	ps
T_{TAP5}	Maximum tap 5 delay	171	194	231	N/A	ps
T_{TAP6}	Maximum tap 6 delay	207	249	292	N/A	ps
T_{TAP7}	Maximum tap 7 delay	212	276	343	N/A	ps
T_{TAP8}	Maximum tap 8 delay	322	341	424	N/A	ps
F_{MINCAL}	Minimum allowed bit rate for calibration in variable mode: VARIABLE_FROM_ZERO, VARIABLE_FROM_HALF_MAX, and DIFF_PHASE_DETECTOR.	188	188	188	N/A	Mb/s
$T_{IODDO\_IDATAIN}$	Propagation delay through IODELAY2	Note 1	Note 1	Note 1	Note 3	–
$T_{IODDO\_ODATAIN}$	Propagation delay through IODELAY2	Note 1	Note 1	Note 1	Note 3	–

Notes:

1. Delay depends on IODELAY2 tap setting. See TRACE report for actual values.
2. Maximum delay = integer (number of taps/8) × T_{TAP8} + T_{TAPn} (where n equals the remainder). For minimum delay consult the TRACE setup and hold report. Minimum delay is typically greater than 30% of the maximum delay. Tap delays can vary by device and overall conditions. See TRACE report for actual values.
3. Spartan-6 -1L devices only support tap 0. See TRACE report for actual values.

CLB Distributed RAM Switching Characteristics (SLICEM Only)

Table 41: **CLB Distributed RAM Switching Characteristics (SLICEM Only)**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
Sequential Delays						
T_{SHCKO}	Clock to A – D outputs	1.26	1.55	1.55	2.35	ns, Max
	Clock to A – D outputs (direct output path)	0.96	1.20	1.20	1.87	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{DS}/T_{DH}	AX – DX or AI – DI inputs to CLK	0.59/ 0.17	0.73/ 0.22	0.73/ 0.22	1.17/ 0.33	ns, Min
T_{AS}/T_{AH}	Address An inputs to clock for XC devices	0.28/ 0.35	0.32/ 0.42	0.32/ 0.42	0.26/ 0.71	ns, Min
	Address An inputs to clock for XA and XQ devices	0.28/ 0.51	N/A	0.32/ 0.51	0.26/ 0.71	ns, Min
T_{WS}/T_{WH}	WE input to clock	0.31/ –0.08	0.37/ –0.08	0.37/ –0.08	0.59/ –0.27	ns, Min
T_{CECK}/T_{CKCE}	CE input to CLK	0.31/ –0.08	0.37/ –0.08	0.37/ –0.08	0.59/ –0.27	ns, Min

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 42: **CLB Shift Register Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
Sequential Delays						
T_{REG}	Clock to A – D outputs	1.35	1.78	1.78	2.74	ns, Max
	Clock to A – D outputs (direct output path)	1.24	1.65	1.65	2.48	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{WS}/T_{WH}	WE input to CLK	0.20/ –0.07	0.24/ –0.07	0.24/ –0.07	0.29/ –0.27	ns, Min
T_{CECK}/T_{CKCE}	CE input to CLK for XC devices	0.30/ 0.30	0.30/ 0.38	0.30/ 0.38	0.82/ –0.41	ns, Min
	CE input to CLK for XA and XQ devices	0.32/ 0.30	N/A	0.40/ 0.38	0.82/ –0.41	ns, Min
T_{DS}/T_{DH}	AX – DX or AI – DI inputs to CLK	0.07/ 0.11	0.09/ 0.14	0.09/ 0.14	0.11/ 0.23	ns, Min

Block RAM Switching Characteristics

Table 43: **Block RAM Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
Block RAM Clock to Out Delays						
T_{RCKO_DO}	Clock CLK to DOUT output (without output register)(1)	1.85	2.10	2.10	3.50	ns, Max
$T_{RCKO\_DO\_REG}$	Clock CLK to DOUT output (with output register)(2)	1.60	1.75	1.75	2.30	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{RCCK_ADDR}/T_{RCKC_ADDR}	ADDR inputs for XC devices(3)	0.35/ 0.10	0.40/ 0.12	0.40/ 0.12	0.50/ 0.15	ns, Min
	ADDR inputs for XA and XQ devices(3)	0.35/ 0.17	N/A	0.40/ 0.17	0.50/ 0.15	ns, Min
T_{RDCK_DI}/T_{RCKD_DI}	DIN inputs(4)	0.30/ 0.10	0.30/ 0.10	0.30/ 0.10	0.40/ 0.15	ns, Min
T_{RCCK_EN}/T_{RCKC_EN}	Block RAM Enable (EN) input	0.22/ 0.05	0.25/ 0.06	0.25/ 0.06	0.44/ 0.10	ns, Min
T_{RCCK_REGCE}/T_{RCKC_REGCE}	CE input of output register	0.20/ 0.10	0.20/ 0.10	0.20/ 0.10	0.28/ 0.15	ns, Min
T_{RCCK_WE}/T_{RCKC_WE}	Write Enable (WE) input	0.25/ 0.10	0.33/ 0.10	0.33/ 0.10	0.28/ 0.15	ns, Min
Maximum Frequency						
F_{MAX}	Block RAM in all modes	320	280	280	150	MHz

Notes:

1. T_{RCKO_DO} includes T_{RCKO_DOA} and T_{RCKO_DOPA} as well as the B port equivalent timing parameters.
2. $T_{RCKO\_DO\_REG}$ includes $T_{RCKO\_DOA\_REG}$ and $T_{RCKO\_DOPA\_REG}$ as well as the B port equivalent timing parameters.
3. The ADDR setup and hold must be met when EN is asserted (even when WE is deasserted). Otherwise, block RAM data corruption is possible.
4. T_{RDCK_DI} includes both A and B inputs as well as the parity inputs of A and B.

Table 67: **Global Clock Input to Output Delay With PLL in Source-Synchronous Mode**

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
LVCMOS25 Global Clock Input to Output Delay using Output Flip-Flop, 12mA, Fast Slew Rate, *with* PLL in Source-Synchronous Mode.							
$T_{ICKOFPLL\_0}$	Global Clock and OUTFF *with* PLL	XC6SLX4	5.49	N/A	7.44	8.55	ns
		XC6SLX9	5.49	6.29	7.44	8.55	ns
		XC6SLX16	5.23	5.77	6.79	8.21	ns
		XC6SLX25	5.00	5.35	6.10	8.54	ns
		XC6SLX25T	5.00	5.35	6.10	N/A	ns
		XC6SLX45	5.59	6.03	7.02	8.39	ns
		XC6SLX45T	5.59	6.03	7.02	N/A	ns
		XC6SLX75	4.96	5.41	6.22	8.32	ns
		XC6SLX75T	4.96	5.41	6.22	N/A	ns
		XC6SLX100	4.97	5.42	6.21	9.08	ns
		XC6SLX100T	5.01	5.42	6.21	N/A	ns
		XC6SLX150	4.59	5.06	5.86	8.13	ns
		XC6SLX150T	4.59	5.06	5.86	N/A	ns
		XA6SLX4	5.79	N/A	7.32	N/A	ns
		XA6SLX9	5.79	N/A	7.32	N/A	ns
		XA6SLX16	5.56	N/A	6.66	N/A	ns
		XA6SLX25	5.40	N/A	5.97	N/A	ns
		XA6SLX25T	5.40	N/A	6.07	N/A	ns
		XA6SLX45	5.89	N/A	6.90	N/A	ns
		XA6SLX45T	5.89	N/A	6.90	N/A	ns
		XA6SLX75	5.27	N/A	6.12	N/A	ns
		XA6SLX75T	5.27	N/A	6.12	N/A	ns
		XA6SLX100	N/A	N/A	6.80	N/A	ns
		XQ6SLX75	N/A	N/A	6.12	8.32	ns
		XQ6SLX75T	5.27	N/A	6.12	N/A	ns
		XQ6SLX150	N/A	N/A	5.88	8.13	ns
		XQ6SLX150T	5.21	N/A	5.88	N/A	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. PLL output jitter is included in the timing calculation.

Table 72: Global Clock Setup and Hold With DCM in System-Synchronous Mode

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for LVCMOS25 Standard.[1]							
T_{PSDCM}/ T_{PHDCM}	No Delay Global Clock and IFF[2] with DCM in System-Synchronous Mode	XC6SLX4	1.54/0.06	N/A	1.75/0.12	2.84/0.27	ns
		XC6SLX9	1.54/0.06	1.63/0.12	1.75/0.12	2.84/0.27	ns
		XC6SLX16	1.72/–0.18	1.87/–0.17	2.13/–0.17	2.31/0.26	ns
		XC6SLX25	1.70/–0.03	1.78/–0.02	2.00/–0.02	2.88/0.20	ns
		XC6SLX25T	1.70/0.07	1.78/0.08	2.00/0.08	N/A	ns
		XC6SLX45	1.74/–0.03	1.84/–0.02	2.02/–0.02	2.64/0.52	ns
		XC6SLX45T	1.74/–0.01	1.84/0.00	2.02/0.00	N/A	ns
		XC6SLX75	1.86/0.11	1.98/0.12	2.20/0.12	2.96/0.58	ns
		XC6SLX75T	1.86/0.11	1.98/0.12	2.20/0.12	N/A	ns
		XC6SLX100	1.64/0.07	1.72/0.08	1.97/0.08	2.70/0.99	ns
		XC6SLX100T	1.64/0.09	1.72/0.10	1.97/0.10	N/A	ns
		XC6SLX150	1.53/0.39	1.62/0.40	1.82/0.40	2.75/1.00	ns
		XC6SLX150T	1.53/0.39	1.62/0.40	1.82/0.40	N/A	ns
		XA6SLX4	1.65/0.16	N/A	1.75/0.26	N/A	ns
		XA6SLX9	1.65/0.16	N/A	1.75/0.26	N/A	ns
		XA6SLX16	1.88/0.02	N/A	2.13/0.03	N/A	ns
		XA6SLX25	1.80/0.16	N/A	2.05/0.17	N/A	ns
		XA6SLX25T	1.80/0.16	N/A	2.13/0.17	N/A	ns
		XA6SLX45	1.75/0.12	N/A	2.02/0.13	N/A	ns
		XA6SLX45T	1.75/0.12	N/A	2.02/0.13	N/A	ns
		XA6SLX75	1.87/0.11	N/A	2.20/0.12	N/A	ns
		XA6SLX75T	1.87/0.11	N/A	2.20/0.12	N/A	ns
		XA6SLX100	N/A	N/A	2.46/0.24	N/A	ns
		XQ6SLX75	N/A	N/A	2.20/0.12	2.96/0.58	ns
		XQ6SLX75T	1.87/0.11	N/A	2.20/0.12	N/A	ns
		XQ6SLX150	N/A	N/A	1.82/0.56	2.75/1.00	ns
		XQ6SLX150T	1.65/0.55	N/A	1.82/0.56	N/A	ns

Notes:

1. Setup and Hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the Global Clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the Global Clock input signal using the fastest process, lowest temperature, and highest voltage. These measurements include DCM CLK0 jitter.
2. IFF = Input Flip-Flop or Latch
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 73: **Global Clock Setup and Hold With DCM in Source-Synchronous Mode**

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for LVCMOS25 Standard.[1]							
T_{PSDCM0}/ T_{PHDCM0}	No Delay Global Clock and IFF[2] with DCM in Source-Synchronous Mode	XC6SLX4	0.71/0.65	N/A	0.72/1.22	1.58/1.18	ns
		XC6SLX9	0.71/0.69	0.71/1.19	0.72/1.36	1.58/1.18	ns
		XC6SLX16	0.86/0.52	0.92/0.57	1.04/0.60	1.02/1.06	ns
		XC6SLX25	0.84/0.58	0.90/0.59	1.01/0.59	1.58/1.07	ns
		XC6SLX25T	0.84/0.58	0.90/0.59	1.01/0.59	N/A	ns
		XC6SLX45	0.85/0.70	0.90/0.76	0.98/0.79	1.34/1.34	ns
		XC6SLX45T	0.85/0.70	0.90/0.76	0.98/0.79	N/A	ns
		XC6SLX75	1.00/0.62	1.06/0.63	1.15/0.63	1.65/1.46	ns
		XC6SLX75T	1.00/0.71	1.06/0.72	1.15/0.72	N/A	ns
		XC6SLX100	0.81/0.68	0.81/0.69	0.94/0.69	1.42/2.07	ns
		XC6SLX100T	0.81/0.68	0.81/0.69	0.94/0.69	N/A	ns
		XC6SLX150	0.68/0.98	0.69/0.99	0.79/0.99	1.45/1.60	ns
		XC6SLX150T	0.68/0.98	0.69/0.99	0.79/0.99	N/A	ns
		XA6SLX4	0.81/0.74	N/A	0.72/1.36	N/A	ns
		XA6SLX9	0.81/0.74	N/A	0.72/1.36	N/A	ns
		XA6SLX16	1.01/0.56	N/A	1.04/0.60	N/A	ns
		XA6SLX25	0.94/0.76	N/A	1.06/0.77	N/A	ns
		XA6SLX25T	0.94/0.76	N/A	1.14/0.77	N/A	ns
		XA6SLX45	0.86/0.74	N/A	0.98/0.78	N/A	ns
		XA6SLX45T	0.86/0.74	N/A	0.98/0.78	N/A	ns
		XA6SLX75	1.02/0.71	N/A	1.15/0.72	N/A	ns
		XA6SLX75T	1.02/0.71	N/A	1.15/0.72	N/A	ns
		XA6SLX100	N/A	N/A	1.37/0.75	N/A	ns
		XQ6SLX75	N/A	N/A	1.15/0.72	1.65/1.46	ns
		XQ6SLX75T	1.02/0.71	N/A	1.15/0.72	N/A	ns
		XQ6SLX150	N/A	N/A	0.79/1.15	1.45/1.60	ns
		XQ6SLX150T	0.73/1.15	N/A	0.79/1.15	N/A	ns

Notes:

1. Setup and Hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the Global Clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the Global Clock input signal using the fastest process, lowest temperature, and highest voltage. These measurements include DCM CLK0 jitter.
2. IFF = Input Flip-Flop or Latch
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Date	Version	Description of Revisions
06/14/10	1.5	In Table 2, added note 5 and added temperature range to V_{FS} and R_{FUSE}. Removed speed grade delineation, revised I_{RPD} description, and updated note 2 in Table 4. Added note 2 to Table 7. Added DIFF_MOBILE_DDR to Table 8 and Table 10. Added note 4 to Table 15. Changed minimum DV_{PPIN} in Table 16. Updated $F_{GTPDRPCLK}$ in Table 19. Increased maximum T_{LLSKEW} in Table 22. Updated descriptions and added data to Table 23. Removed note 1 and added new data to the Networking Applications section in Table 25. Updated Table 26 and Table 27 to the data in ISE v12.1 software with speed specification v1.08. In Table 28, added DIFF_MOBILE_DDR and updated -4 speed grade data. Updated the maximum I/O pairs per bank in Table 33. Updated note 2 on Table 39. Revised the F_{MAX} in Table 44. In Table 47, updated description for $T_{SMCKCSO}$, revised values for T_{POR} and added Min value, added $T_{BPIICCK}$ and $T_{SPIICCK}$. Also in Table 47, added device dependencies to F_{SMCCK} and F_{RBCCK}. Updated and added data to Table 63 through Table 78, and Table 81. In Table 79, added data on the XC6SLX45-FG(G)676 and revised the XC6SLX45T and XC6SLX150T values. The following changes to this specification are addressed in the product change notice XCN10024, *MCB Performance and JTAG Revision Code for Spartan-6 LX16 and LX45 FPGAs*. In Table 2, revised the V_{CCINT} to add the memory controller block extended performance specifications. In Table 25, changed the standard specifications and added extended performance specifications for the memory controller block and note 2. Added note 4 and updated values in Table 34.
06/24/10	1.6	Production release of XC6SLX45T (-2 and -3 speed grades), XC6SLX16 and XC6SLX45 (-3 speed grade) devices which includes changes to Table 26 and Table 27 (ISE v12.1 software with speed specification v1.08). Added the -3N speed grade, which designates Spartan-6 devices that do not support MCB functionality. This includes changes to Table 2 (note 2), Table 25 (note 4), and Switching Characteristics (Table 26). Updated Simultaneously Switching Outputs discussion. Added -3 speed grade values for T_{TAP} and F_{MINCAL} values in Table 39. In Table 40, updated T_{RPW} (-2 and -3 speed grade) values and F_{TOG} (-3 speed grade) values. In Table 48, updated T_{GIO} (-2 and -3 speed grade) values. Updated -3 values in spread spectrum section of Table 57.
07/16/10	1.7	Production release of specific devices listed in Table 26 and Table 27 using ISE v12.2 software with speed specification v1.11. Added note 4 advising designers of the patch which contains v1.11. Also updated the -1L speed specification to v1.04. Updated numerous -4 and -1L values. Added -4 T_{TAP} values and F_{MINCAL} to Table 39. Revised T_{CINCK}/T_{CKCIN} in Table 40. In Table 41, revised T_{SHCKO}. In Table 42, revised T_{REG}. Added new -1L values to Table 47. Added and updated values in Table 79.
07/26/10	1.8	Production release of XC6SLX25, XC6SLX25T, XC6SLX100 and XC6SLX100T in the specific speed grades listed in Table 26 and Table 27 using ISE v12.2 software with speed specification v1.11. Added note 7 to Table 2 and moved V_{FS} and R_{FUSE} to a new Table 3. Added I_{HS} and note 4 to Table 4. Added note 1 to Table 28. Added and updated SSO limits per V_{CCO}/GND pairs in Table 34. Added note 3 to Table 47. In Table 54, removed -1L specifications for CLKOUT_PER_JITT_DV1/2 and revised CLKIN_CLKFB_PHASE and CLKOUT_PHASE_DLL values. Updated note 3 in both Table 56 and Table 57.
08/23/10	1.9	Updated values for $F_{GTPRANGE1}$, $F_{GTPRANGE2}$, and $F_{GPLLMIN}$ in Table 18. Revised -3 and -4 values in Table 21. Removed the -1L speed grade readback support restriction and note 3 in Table 47.
11/05/10	1.10	Production release of XC6SLX4 and XC6SLX9 in the specific speed grades listed in Table 26 and Table 27 using ISE v12.3 software with speed specification v1.12 for the -2 speed grade available in the 12.3 *Speed Files Patch*. Added note 3 advising designers of the patch which contains v1.12. In Table 2, added note 4. In Table 4, added note 2. In Table 10, added notes 2 and 3. In Table 44, added note 2. In Table 47, updated symbol for T_{SMWCCK}/T_{SMCCKW}, changed -1L values for $T_{USERCCLKH}$ and $T_{USERCCLKL}$, and added and revised the modes for F_{MCCK} and F_{SMCCK}. In Table 53, redefined and expanded description for CLKIN_FREQ_DLL and rewrote note 3. Updated title of Table 58. Also in Table 78, revised T_{DCD_CLK} for XC6SLX150 and XC6SLX150T. Changed description of T_{PSFD}/ T_{PHFD} in Table 71. For the -1L speed grade, updated data sheet to ISE 12.3 software with speed specification v1.05 which revised the values in the following tables: Table 25, Table 28, Table 35, Table 36, Table 37, Table 40 through Table 43, Table 48 through Table 56, Table 62 through Table 78, Table 80, and Table 81. Updated Notice of Disclaimer.

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